

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT78 plastic package intended for use in applications requiring high bidirectional blocking voltage capability, high surge current capability and high thermal cycling performance.

2. Features and benefits

- High bidirectional blocking voltage capability
- High surge current capability
- High thermal cycling performance

3. Applications

- Ignition circuits
- Motor control
- Protection circuits
- Voltage regulation

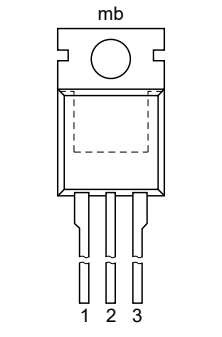

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	650	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 109\text{ °C}$; Fig. 1	-	-	7.5	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 109\text{ °C}$; Fig. 2 ; Fig. 3	-	-	12	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	-	-	120	A
		half sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$	-	-	132	A
T_j	junction temperature		-	-	125	°C
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 7	-	2	15	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 436\text{ V}$; $T_j = 125\text{ °C}$; $R_{GK} = 100\text{ }\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; Fig. 12	200	1000	-	V/ μ s

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 <p>TO-220AB (SOT78)</p>	 <p>sym037</p>
2	A	anode		
3	G	gate		
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

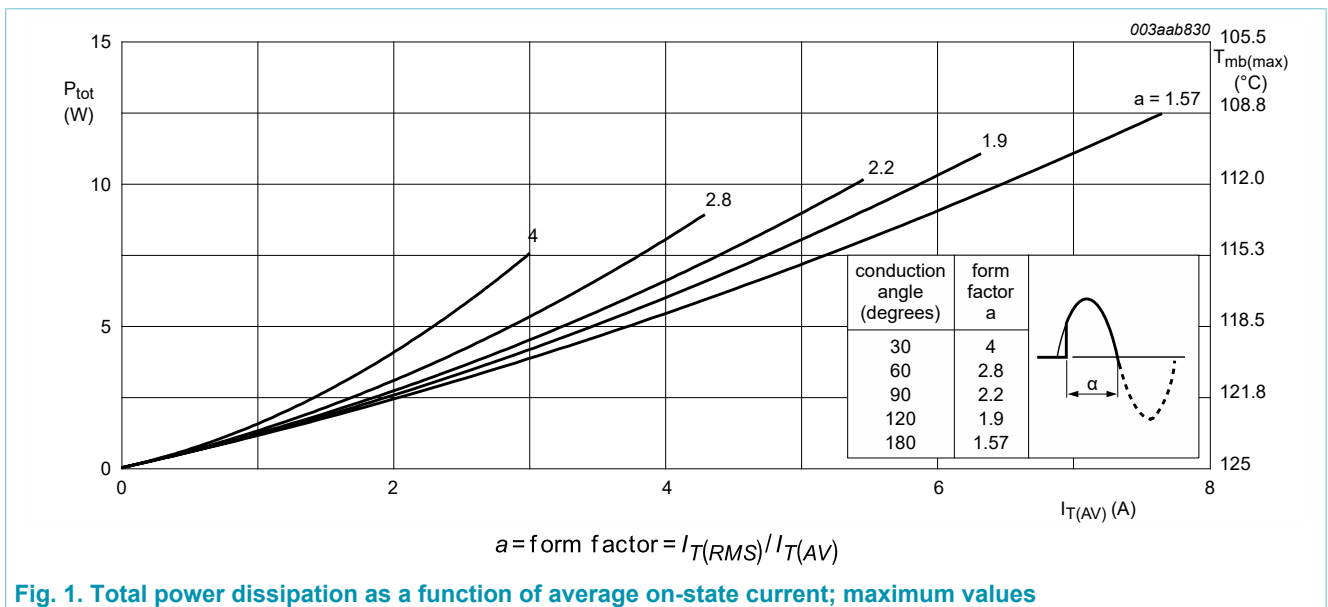
Type number	Package		
	Name	Description	Version
BT151-650R	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	650	V
V_{RRM}	repetitive peak reverse voltage		-	650	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 109\text{ }^{\circ}\text{C}$; Fig. 1	-	7.5	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 109\text{ }^{\circ}\text{C}$; Fig. 2 ; Fig. 3	-	12	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	-	120	A
		half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$	-	132	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	72	A^2s
di_T/dt	rate of rise of on-state current	$I_G = 30\text{ mA}$	-	50	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	2	A
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_j	junction temperature		-	125	$^{\circ}\text{C}$



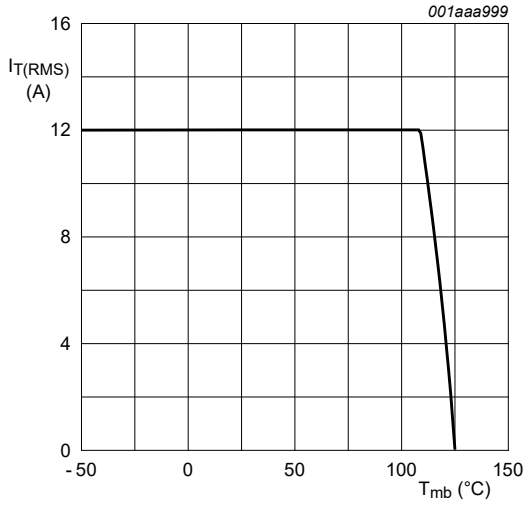
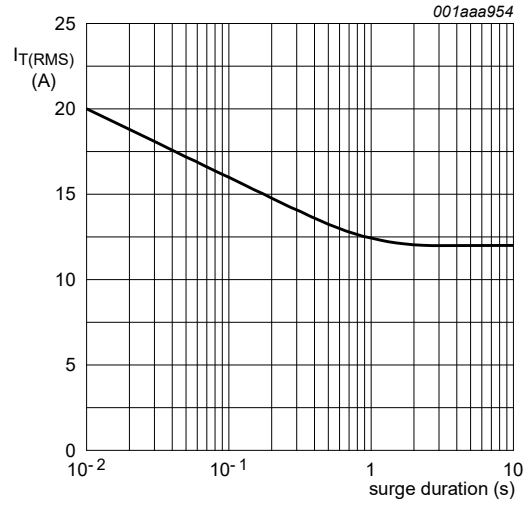


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



$f = 50 \text{ Hz}, T_{mb} = 109^\circ\text{C}$

Fig. 3. RMS on-state current as a function of surge duration; maximum values

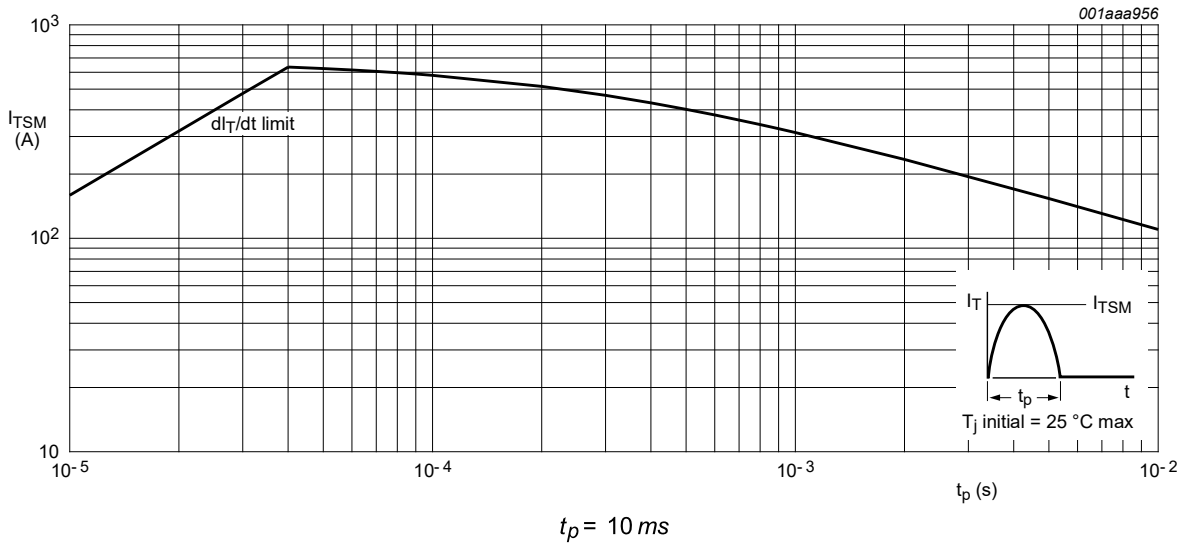
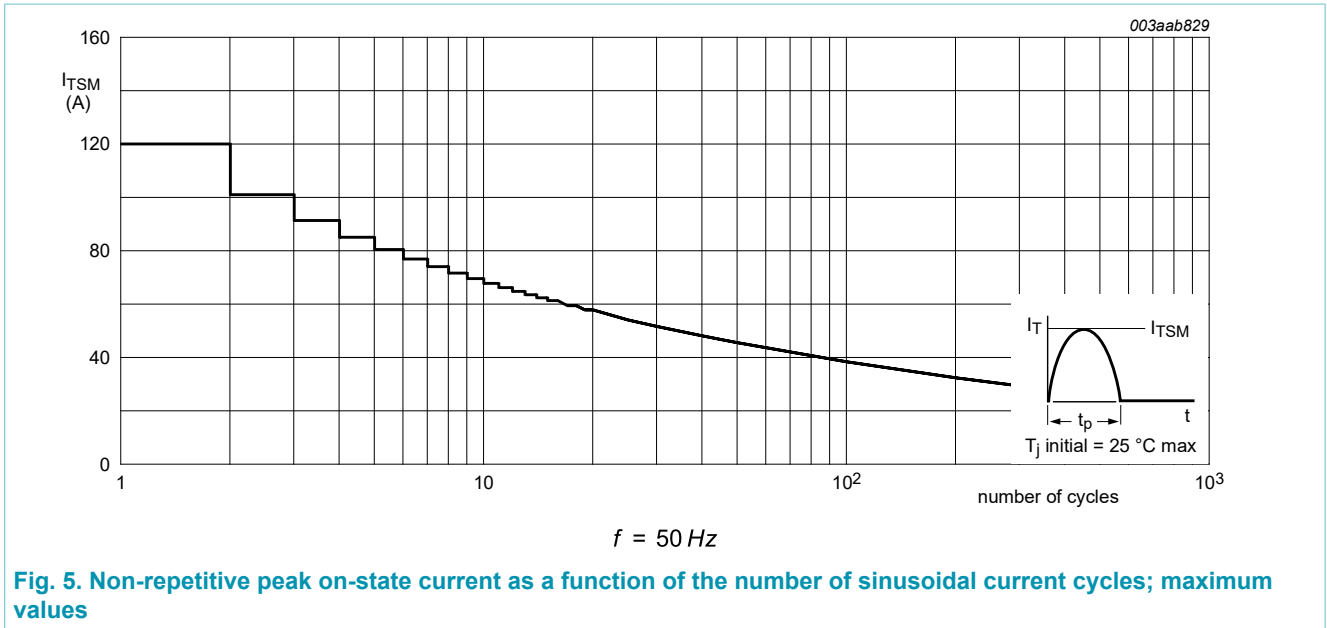


Fig. 4. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 6	-	-	1.3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

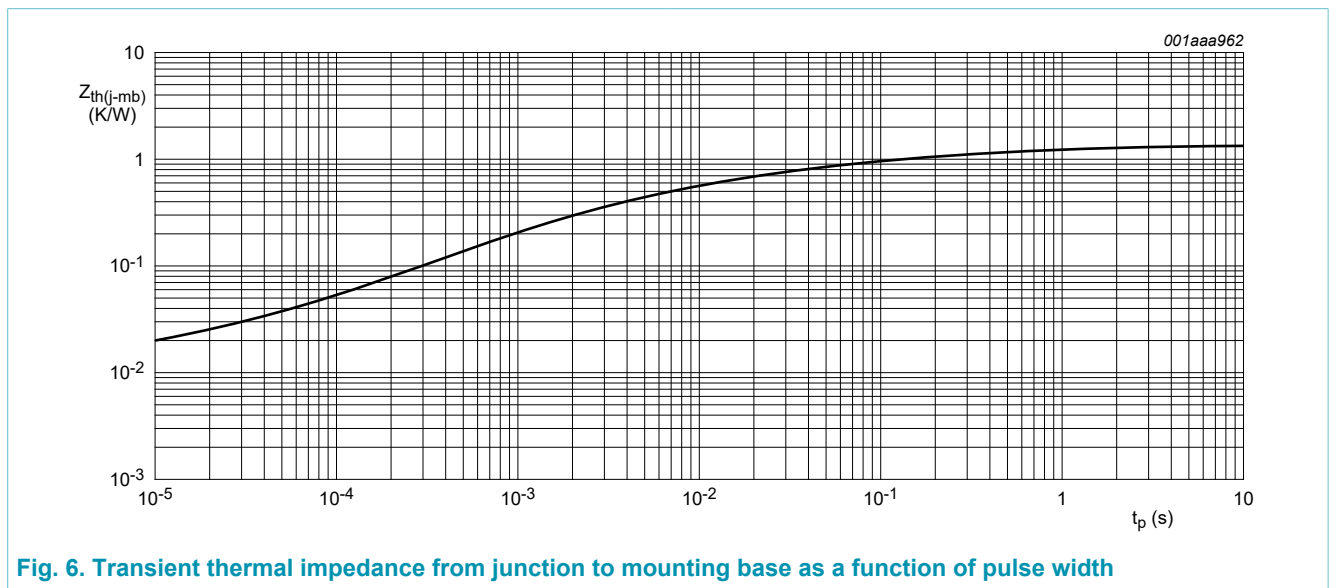
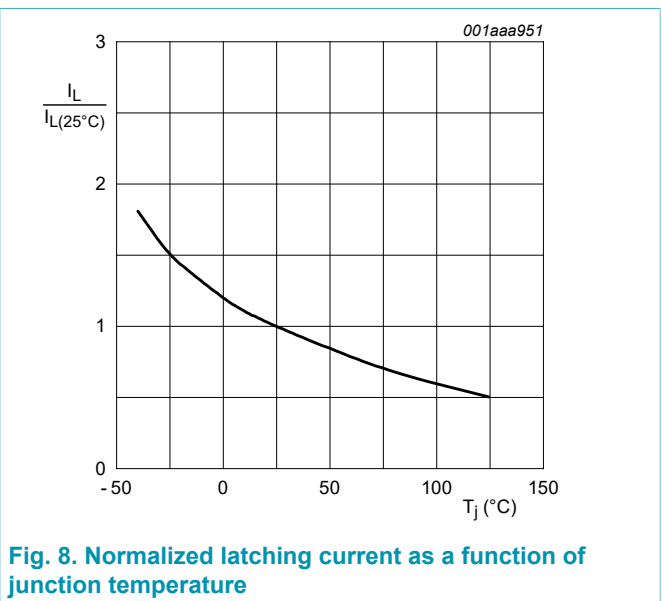
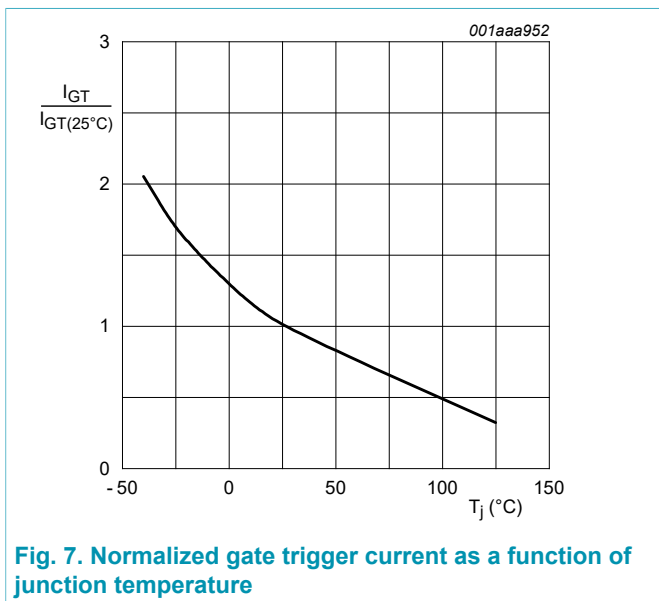


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 7	-	2	15	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 8	-	10	40	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 9	-	7	20	mA
V_T	on-state voltage	$I_T = 23\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	1.4	1.75	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 11	-	0.6	1.5	V
		$V_D = 650\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$; Fig. 11	0.25	0.4	-	V
I_D	off-state current	$V_D = 650\text{ V}$; $T_j = 125\text{ °C}$	-	0.1	0.5	mA
I_R	reverse current	$V_R = 650\text{ V}$; $T_j = 125\text{ °C}$	-	0.1	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 436\text{ V}$; $T_j = 125\text{ °C}$; $R_{GK} = 100\text{ }\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; Fig. 12	200	1000	-	V/ μ s
		$V_{DM} = 436\text{ V}$; $T_j = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit; Fig. 12	50	130	-	V/ μ s
t_{gt}	gate-controlled turn-on time	$I_{TM} = 40\text{ A}$; $V_D = 650\text{ V}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$	-	2	-	μ s
t_q	commutated turn-off time	$V_{DM} = 436\text{ V}$; $T_j = 125\text{ °C}$; $I_{TM} = 20\text{ A}$; $V_R = 25\text{ V}$; $(dI_T/dt)_M = 30\text{ A}/\mu\text{s}$; $dV_D/dt = 50\text{ V}/\mu\text{s}$; $R_{GK(ext)} = 100\text{ }\Omega$; ($V_{DM} = 67\%$ of V_{DRM})	-	70	-	μ s



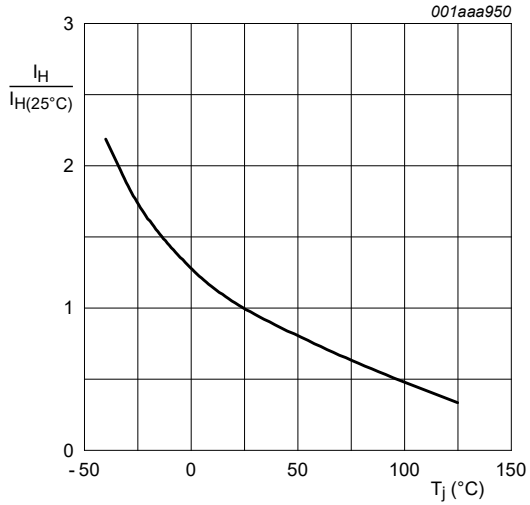
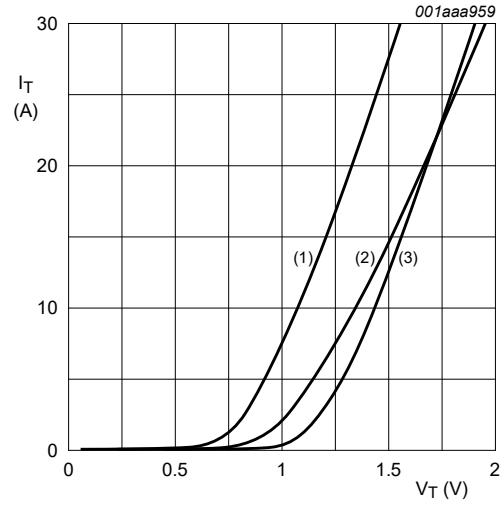


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.06 \text{ V}; R_s = 0.0304 \ \Omega$

- (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
- (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

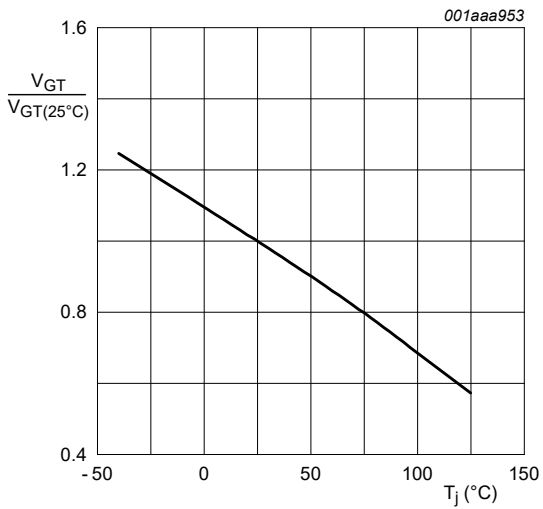
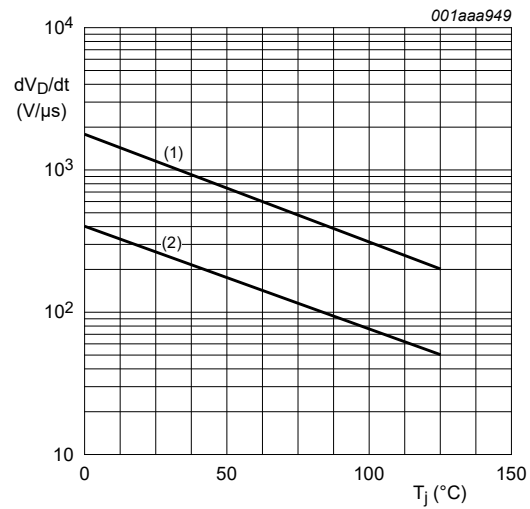


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

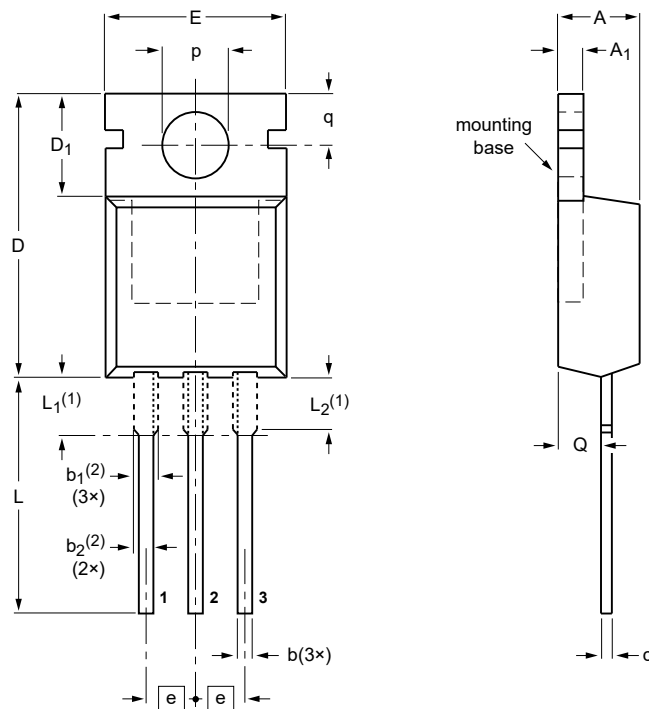


- (1) $R_{GK} = 100 \ \Omega$;
- (2) gate open circuit

Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

10. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (2)	b ₂ (2)	c	D	D ₁	E	e	L	L ₁ (1)	L ₂ (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig. 13. Package outline TO-220AB (SOT78)

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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